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IN THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in

the application:

Listing of Claims

1-10. Canceled.

11. (Currently Amended) A method of producing a I-III-VI_y compound in

thin film form by electrochemistry, in which y is close to 2, and VI is an element comprising

selenium, I is copper, silver or gold and III is boron, aluminum, gallium, indium or thallium,

comprising:

a) providing an electrolysis bath comprising active selenium, in oxidation

state IV (Se(IV)), and at least two electrodes;

b) applying a potential difference between the two electrodes to promote

migration of the active selenium toward one of the electrodes and initiate formation of at

least one thin film of the I-III-VI_v compound; and,

c) regenerating the selenium in active form (Se(IV)) in the electrolysis

bath.

12. (Previously Presented) The method of Claim 11, wherein, at step c), an

oxidizing agent for selenium is introduced into the electrolysis bath in order to regenerate the

selenium in active form.

13. (Previously Presented) The method of Claim 12, wherein when the

electrolysis bath contains selenium in colloid form (Se(0)) at step b), the oxidizing agent

regenerates the selenium in the colloid form to selenium in the active form.

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14. (Previously Presented) The method of Claim 12, wherein the oxidizing

agent is hydrogen peroxide (H₂O₂).

15. (Previously Presented) The method of Claim 14, wherein the hydrogen

peroxide is added to the electrolysis bath in a concentration at least approximately five times

an initial selenium concentration in the electrolysis bath.

16. (Previously Presented) The method of Claim 11, wherein, at step c),

selenium is added to the electrolysis bath in order to form an excess of active selenium in the

electrolysis bath.

17. (Previously Presented) The method of Claim 11, wherein, when one

tenth of a concentration of selenium at step a) is consumed by producing the thin film at step

b), approximately twice the consumed concentration of selenium is added to the bath at step

c).

18. (Previously Presented) The method of Claim 11, wherein, after step c),

at least one new thin film of the I-III-VI_v compound is formed.

19. (Previously Presented) The method of Claim 11, wherein, the at least

one thin film of the I-III-VI_v compound is CuInSe_v and the bath further comprises, at step a),

for one unit of concentration of copper in the electrolysis bath, about 1.7 units of

concentration of the active selenium.

20. (Previously Presented) The method of Claim 11, further comprising

step d), regenerating the electrolysis bath by introducing oxides and/or hydroxides of

elements I and III wherein, the oxide is In₂O₃ and the hydroxide is In(OH)₃, or wherein the

oxide is CuO and the hydroxide is $Cu(OH)_2$.

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